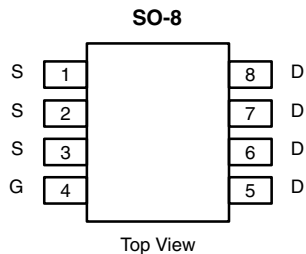




## N-Channel 100 V (D-S) MOSFET

### PRODUCT SUMMARY

| V <sub>DS</sub> (V) | R <sub>DS(on)</sub> (Ω) Max.      | I <sub>D</sub> (A) <sup>a</sup> | Q <sub>g</sub> (Typ.) |
|---------------------|-----------------------------------|---------------------------------|-----------------------|
| 100                 | 0.0100 at V <sub>GS</sub> = 10 V  | 19.7                            | 27.9 nC               |
|                     | 0.0105 at V <sub>GS</sub> = 7.5 V | 19.2                            |                       |
|                     | 0.0120 at V <sub>GS</sub> = 6.0 V | 18                              |                       |


**Ordering Information:**

Si4090DY-T1-GE3 (Lead (Pb)-free and Halogen-free)

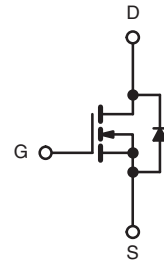
### FEATURES

- TrenchFET<sup>®</sup> Power MOSFET
- 100 % R<sub>g</sub> and UIS Tested
- Material categorization:  
For definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)


**RoHS**  
 COMPLIANT  
 HALOGEN  
**FREE**

### APPLICATIONS

- DC/DC Primary Side Switch
- Telecom/Server
- Motor Drive Control
- Synchronous Rectification



N-Channel MOSFET

### ABSOLUTE MAXIMUM RATINGS (T<sub>A</sub> = 25 °C, unless otherwise noted)

| Parameter                                          |                        | Symbol                            | Limit                | Unit |
|----------------------------------------------------|------------------------|-----------------------------------|----------------------|------|
| Drain-Source Voltage                               |                        | V <sub>DS</sub>                   | 100                  | V    |
| Gate-Source Voltage                                |                        | V <sub>GS</sub>                   | ± 20                 |      |
| Continuous Drain Current (T <sub>J</sub> = 150 °C) | T <sub>C</sub> = 25 °C | I <sub>D</sub>                    | 19.7                 | A    |
|                                                    | T <sub>C</sub> = 70 °C |                                   | 15.8                 |      |
|                                                    | T <sub>A</sub> = 25 °C |                                   | 13.2 <sup>b, c</sup> |      |
|                                                    | T <sub>A</sub> = 70 °C |                                   | 10.4 <sup>b, c</sup> |      |
| Pulsed Drain Current (t = 300 μs)                  |                        | I <sub>DM</sub>                   | 70                   |      |
| Continuous Source-Drain Diode Current              | T <sub>C</sub> = 25 °C | I <sub>S</sub>                    | 7                    |      |
|                                                    | T <sub>A</sub> = 25 °C |                                   | 3.1 <sup>b, c</sup>  |      |
| Single Pulse Avalanche Current                     | L = 0.1 mH             | I <sub>AS</sub>                   | 30                   |      |
| Avalanche Energy                                   |                        | E <sub>AS</sub>                   | 45                   | mJ   |
| Maximum Power Dissipation                          | T <sub>C</sub> = 25 °C | P <sub>D</sub>                    | 7.8                  | W    |
|                                                    | T <sub>C</sub> = 70 °C |                                   | 5                    |      |
|                                                    | T <sub>A</sub> = 25 °C |                                   | 3.5 <sup>b, c</sup>  |      |
|                                                    | T <sub>A</sub> = 70 °C |                                   | 2.2 <sup>b, c</sup>  |      |
| Operating Junction and Storage Temperature Range   |                        | T <sub>J</sub> , T <sub>stg</sub> | - 55 to 150          | °C   |

### THERMAL RESISTANCE RATINGS

| Parameter                                   | Symbol            | Typical | Maximum | Unit |
|---------------------------------------------|-------------------|---------|---------|------|
| Maximum Junction-to-Ambient <sup>b, d</sup> | R <sub>thJA</sub> | 29      | 35      | °C/W |
| Maximum Junction-to-Foot (Drain)            | R <sub>thJF</sub> | 13      | 16      |      |

Notes:

 a. Based on T<sub>C</sub> = 25 °C.

b. Surface mounted on 1" x 1" FR4 board.

c. t = 10 s.

d. Maximum under steady state conditions is 80 °C/W.

## Si4090DY

Vishay Siliconix



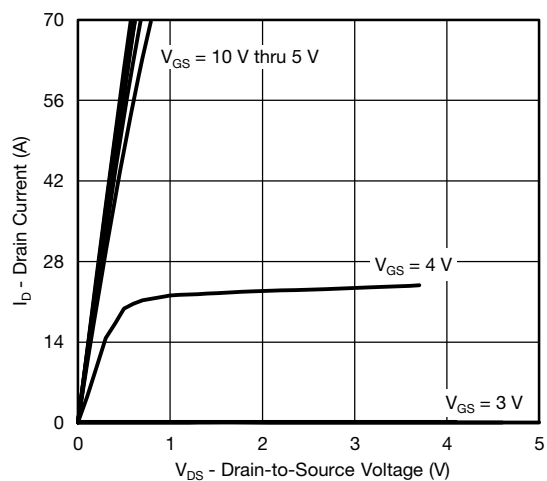
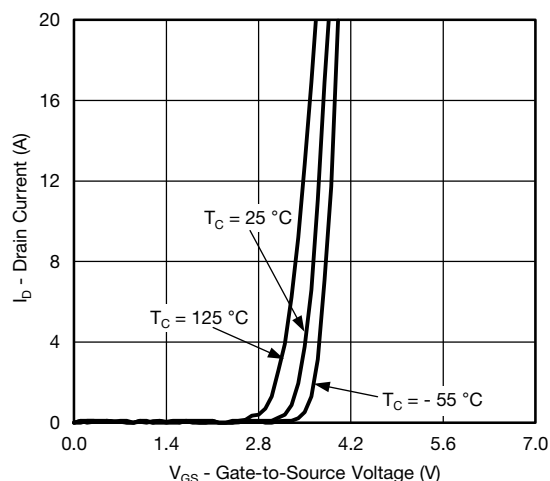
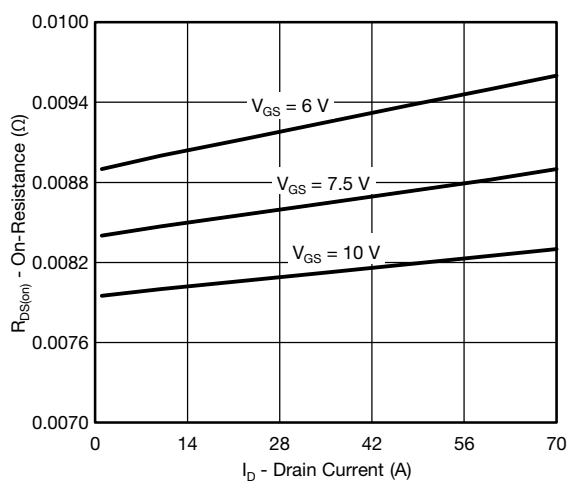
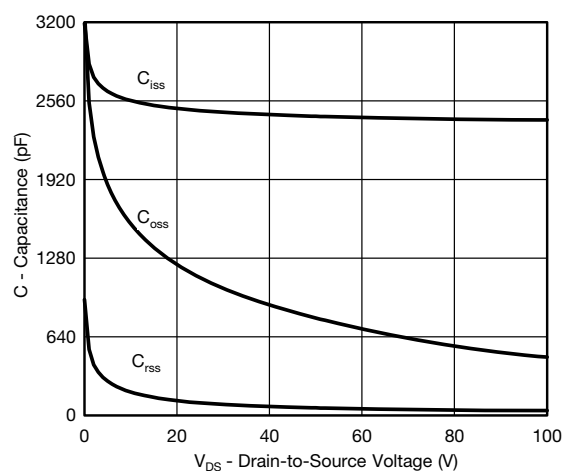
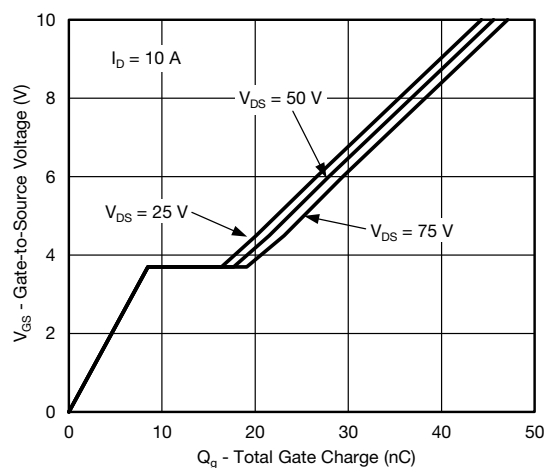
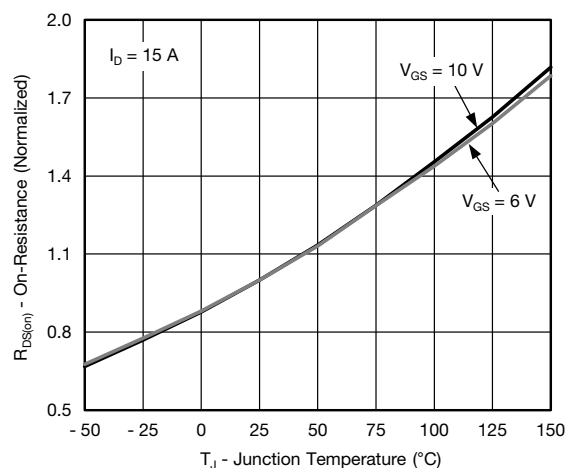
| SPECIFICATIONS (T <sub>J</sub> = 25 °C, unless otherwise noted) |                                      |                                                                                                                       |      |        |        |       |
|-----------------------------------------------------------------|--------------------------------------|-----------------------------------------------------------------------------------------------------------------------|------|--------|--------|-------|
| Parameter                                                       | Symbol                               | Test Conditions                                                                                                       | Min. | Typ.   | Max.   | Unit  |
| Static                                                          |                                      |                                                                                                                       |      |        |        |       |
| Drain-Source Breakdown Voltage                                  | V <sub>DS</sub>                      | V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA                                                                        | 100  |        |        | V     |
| V <sub>DS</sub> Temperature Coefficient                         | ΔV <sub>DS</sub> /T <sub>J</sub>     | I <sub>D</sub> = 250 μA                                                                                               |      | 67     |        | mV/°C |
| V <sub>GS(th)</sub> Temperature Coefficient                     | ΔV <sub>GS(th)</sub> /T <sub>J</sub> |                                                                                                                       |      | - 6.4  |        |       |
| Gate-Source Threshold Voltage                                   | V <sub>GS(th)</sub>                  | V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA                                                           | 2    |        | 3.3    | V     |
| Gate-Source Leakage                                             | I <sub>GSS</sub>                     | V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ± 20 V                                                                       |      |        | ± 100  | nA    |
| Zero Gate Voltage Drain Current                                 | I <sub>DSS</sub>                     | V <sub>DS</sub> = 100 V, V <sub>GS</sub> = 0 V                                                                        |      |        | 1      | μA    |
|                                                                 |                                      | V <sub>DS</sub> = 100 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 55 °C                                                |      |        | 10     |       |
| On-State Drain Current <sup>a</sup>                             | I <sub>D(on)</sub>                   | V <sub>DS</sub> ≥ 5 V, V <sub>GS</sub> = 10 V                                                                         | 30   |        |        | A     |
| Drain-Source On-State Resistance <sup>a</sup>                   | R <sub>DS(on)</sub>                  | V <sub>GS</sub> = 10 V, I <sub>D</sub> = 15 A                                                                         |      | 0.0080 | 0.0100 | Ω     |
|                                                                 |                                      | V <sub>GS</sub> = 7.5 V, I <sub>D</sub> = 12 A                                                                        |      | 0.0085 | 0.0105 |       |
|                                                                 |                                      | V <sub>GS</sub> = 6.0 V, I <sub>D</sub> = 10 A                                                                        |      | 0.0090 | 0.0120 |       |
| Forward Transconductance <sup>a</sup>                           | g <sub>fs</sub>                      | V <sub>DS</sub> = 15 V, I <sub>D</sub> = 15 A                                                                         |      | 54     |        | S     |
| Dynamic <sup>b</sup>                                            |                                      |                                                                                                                       |      |        |        |       |
| Input Capacitance                                               | C <sub>iss</sub>                     | V <sub>DS</sub> = 50 V, V <sub>GS</sub> = 0 V, f = 1 MHz                                                              |      | 2410   |        | pF    |
| Output Capacitance                                              | C <sub>oss</sub>                     |                                                                                                                       |      | 790    |        |       |
| Reverse Transfer Capacitance                                    | C <sub>rss</sub>                     |                                                                                                                       |      | 60     |        |       |
| Total Gate Charge                                               | Q <sub>g</sub>                       | V <sub>DS</sub> = 50 V, V <sub>GS</sub> = 10 V, I <sub>D</sub> = 10 A                                                 |      | 45.6   | 69     | nC    |
|                                                                 |                                      | V <sub>DS</sub> = 50 V, V <sub>GS</sub> = 6 V, I <sub>D</sub> = 10 A                                                  |      | 27.9   | 42     |       |
| Gate-Source Charge                                              | Q <sub>gs</sub>                      |                                                                                                                       |      | 8.5    |        |       |
| Gate-Drain Charge                                               | Q <sub>gd</sub>                      |                                                                                                                       |      | 9.2    |        |       |
| Output Charge                                                   | Q <sub>oss</sub>                     | V <sub>DS</sub> = 50 V, V <sub>GS</sub> = 0 V                                                                         |      | 63     | 95     |       |
| Gate Resistance                                                 | R <sub>g</sub>                       | f = 1 MHz                                                                                                             | 0.4  | 1.3    | 2.6    | Ω     |
| Turn-On Delay Time                                              | t <sub>d(on)</sub>                   | V <sub>DD</sub> = 50 V, R <sub>L</sub> = 5 Ω<br>I <sub>D</sub> ≅ 10 A, V <sub>GEN</sub> = 7.5 V, R <sub>g</sub> = 1 Ω |      | 16     | 32     | ns    |
| Rise Time                                                       | t <sub>r</sub>                       |                                                                                                                       |      | 11     | 22     |       |
| Turn-Off Delay Time                                             | t <sub>d(off)</sub>                  |                                                                                                                       |      | 35     | 70     |       |
| Fall Time                                                       | t <sub>f</sub>                       |                                                                                                                       |      | 10     | 20     |       |
| Turn-On Delay Time                                              | t <sub>d(on)</sub>                   | V <sub>DD</sub> = 50 V, R <sub>L</sub> = 5 Ω<br>I <sub>D</sub> ≅ 10 A, V <sub>GEN</sub> = 10 V, R <sub>g</sub> = 1 Ω  |      | 14     | 28     |       |
| Rise Time                                                       | t <sub>r</sub>                       |                                                                                                                       |      | 10     | 20     |       |
| Turn-Off Delay Time                                             | t <sub>d(off)</sub>                  |                                                                                                                       |      | 36     | 70     |       |
| Fall Time                                                       | t <sub>f</sub>                       |                                                                                                                       |      | 10     | 20     |       |
| Drain-Source Body Diode Characteristics                         |                                      |                                                                                                                       |      |        |        |       |
| Continuous Source-Drain Diode Current                           | I <sub>S</sub>                       | T <sub>C</sub> = 25 °C                                                                                                |      |        | 7      | A     |
| Pulse Diode Forward Current <sup>a</sup>                        | I <sub>SM</sub>                      |                                                                                                                       |      |        | 70     |       |
| Body Diode Voltage                                              | V <sub>SD</sub>                      | I <sub>S</sub> = 5 A                                                                                                  |      | 0.75   | 1.1    | V     |
| Body Diode Reverse Recovery Time                                | t <sub>rr</sub>                      | I <sub>F</sub> = 10 A, di/dt = 100 A/μs, T <sub>J</sub> = 25 °C                                                       |      | 49     | 95     | ns    |
| Body Diode Reverse Recovery Charge                              | Q <sub>rr</sub>                      |                                                                                                                       |      | 58     | 115    | nC    |
| Reverse Recovery Fall Time                                      | t <sub>a</sub>                       |                                                                                                                       |      | 21     |        | ns    |
| Reverse Recovery Rise Time                                      | t <sub>b</sub>                       |                                                                                                                       |      | 28     |        |       |

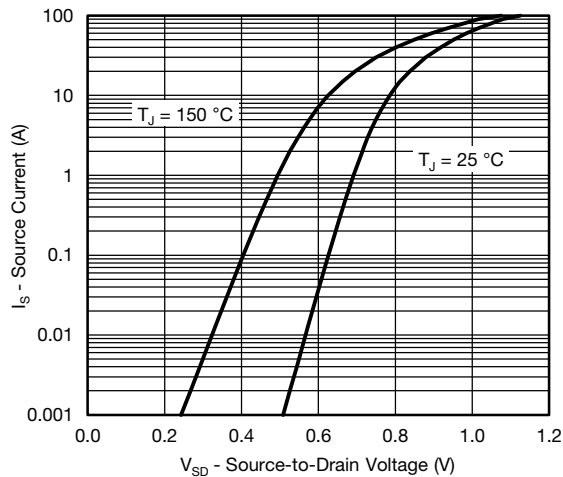
Notes:

a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ 

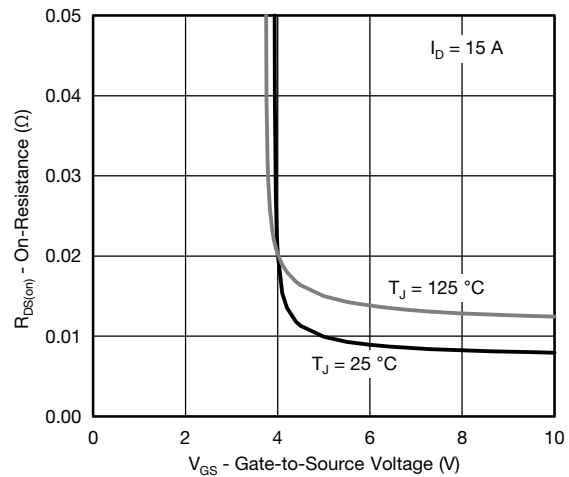
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

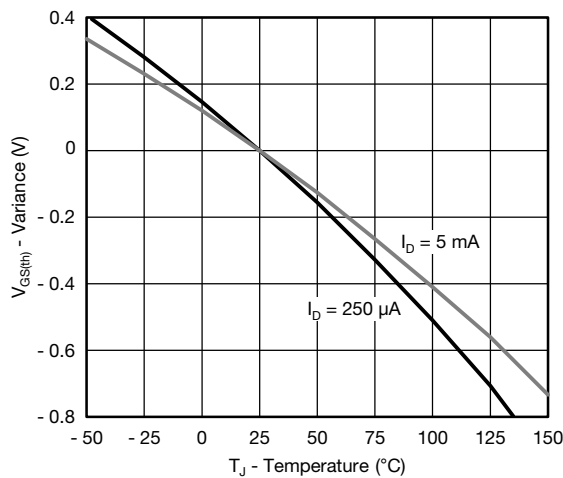

**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)

**Output Characteristics**

**Transfer Characteristics**

**On-Resistance vs. Drain Current**

**Capacitance**

**Gate Charge**

**On-Resistance vs. Junction Temperature**

**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)

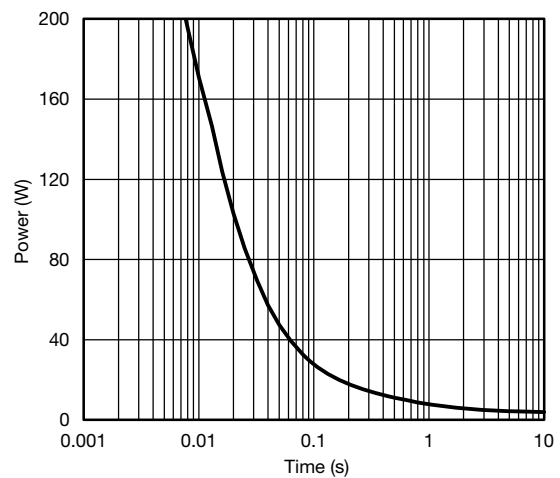
Source-Drain Diode Forward Voltage



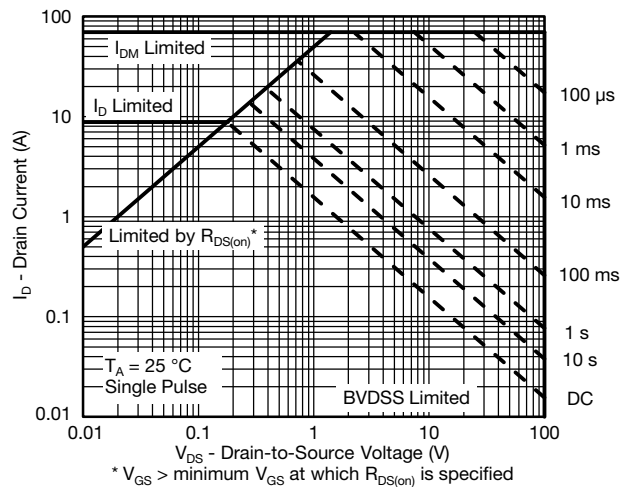
On-Resistance vs. Gate-to-Source Voltage



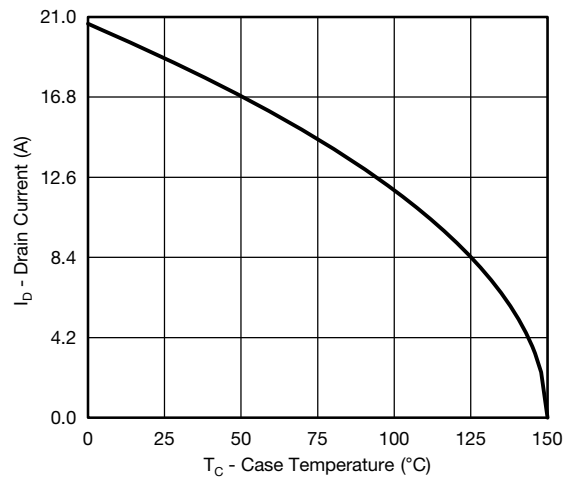
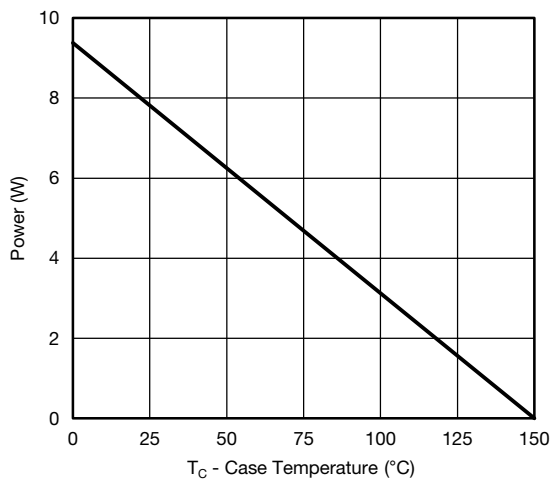
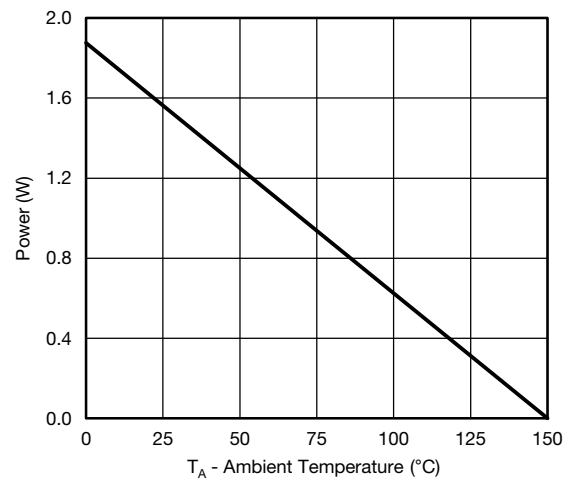
Threshold Voltage



Single Pulse Power, Junction-to-Ambient



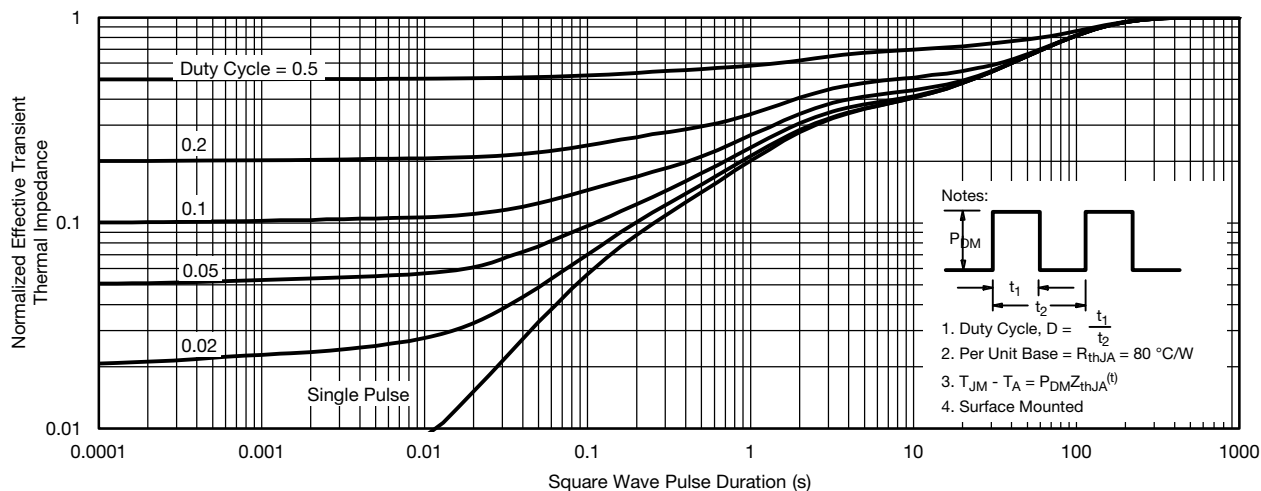
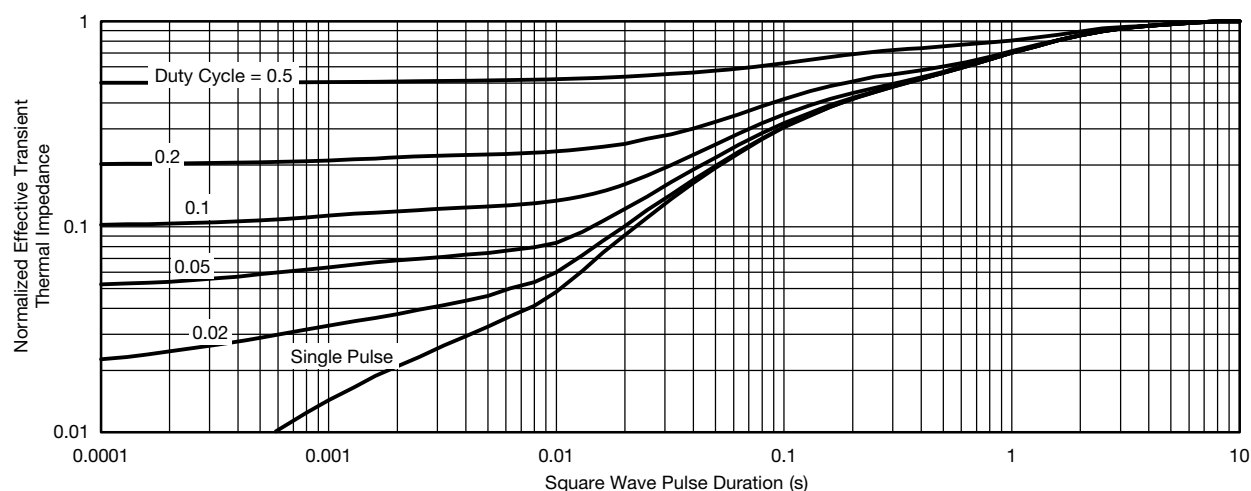
Safe Operating Area, Junction-to-Ambient


**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)

**Current Derating\***

**Power, Junction-to-Foot**

**Power, Junction-to-Ambient**

\* The power dissipation  $P_D$  is based on  $T_{J(max)} = 150$  °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

## Si4090DY

Vishay Siliconix

**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)**Normalized Thermal Transient Impedance, Junction-to-Ambient****Normalized Thermal Transient Impedance, Junction-to-Foot**

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see [www.vishay.com/ppg?63917](http://www.vishay.com/ppg?63917).



## SOIC (NARROW): 8-LEAD

JEDEC Part Number: MS-012



| DIM                            | MILLIMETERS |      | INCHES    |       |
|--------------------------------|-------------|------|-----------|-------|
|                                | Min         | Max  | Min       | Max   |
| A                              | 1.35        | 1.75 | 0.053     | 0.069 |
| A <sub>1</sub>                 | 0.10        | 0.20 | 0.004     | 0.008 |
| B                              | 0.35        | 0.51 | 0.014     | 0.020 |
| C                              | 0.19        | 0.25 | 0.0075    | 0.010 |
| D                              | 4.80        | 5.00 | 0.189     | 0.196 |
| E                              | 3.80        | 4.00 | 0.150     | 0.157 |
| e                              | 1.27 BSC    |      | 0.050 BSC |       |
| H                              | 5.80        | 6.20 | 0.228     | 0.244 |
| h                              | 0.25        | 0.50 | 0.010     | 0.020 |
| L                              | 0.50        | 0.93 | 0.020     | 0.037 |
| q                              | 0°          | 8°   | 0°        | 8°    |
| S                              | 0.44        | 0.64 | 0.018     | 0.026 |
| ECN: C-06527-Rev. I, 11-Sep-06 |             |      |           |       |
| DWG: 5498                      |             |      |           |       |

## RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads  
Dimensions in Inches/(mm)

[Return to Index](#)



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